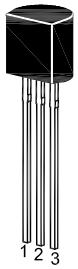
2SC5344

NPN Silicon Epitaxial Planar Transistor

Audio power amplifier applications.

The transistor is subdivided into two groups O and Y according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base
TO-92 Plastic Package

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	35	V
Collector Emitter Voltage	V_{CEO}	30	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_C	800	mA
Collector Dissipation	P_{tot}	625	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	- 55 to + 150	°C

Characteristics at T_a = 25 °C

Parameter			Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at V_{CE} = 1 V, I_C = 100 mA	Current Gain Group	O	h_{FE}	100	-	200	-
		Y	h_{FE}	160	-	320	-
Collector Base Cutoff Current at V_{CB} = 35 V			I_{CBO}	-	-	0.1	µA
Emitter Base Cutoff Current at V_{EB} = 5 V			I_{EBO}	-	-	0.1	µA
Collector Base Breakdown Voltage at I_C = 100 µA			V_{CBO}	35	-	-	V
Collector Emitter Breakdown Voltage at I_C = 10 mA			V_{CEO}	30	-	-	V
Emitter Base Breakdown Voltage at I_E = 10 µA			V_{EBO}	5	-	-	V
Collector-Emitter Saturation Voltage at I_C = 500 mA, I_B = 50 mA			$V_{CE(sat)}$	-	-	0.5	V
Transition Frequency at V_{CE} = 5 V, I_C = 10 mA			f_T	-	120	-	MHz
Collector Output Capacitance at V_{CB} = 10 V, f = 1 MHz			C_{ob}	-	13	-	pF

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Fig. 1 P_C - T_a

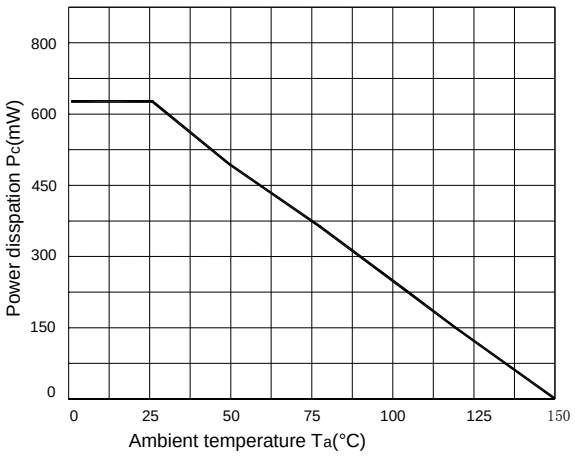

Fig. 2 I_C - V_{BE}

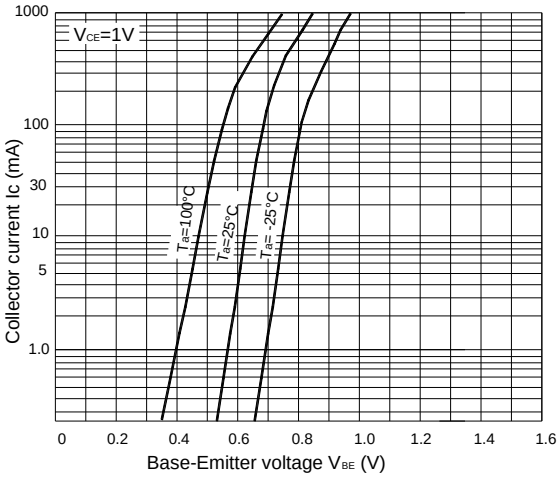

Fig. 3 I_C - V_{CE}

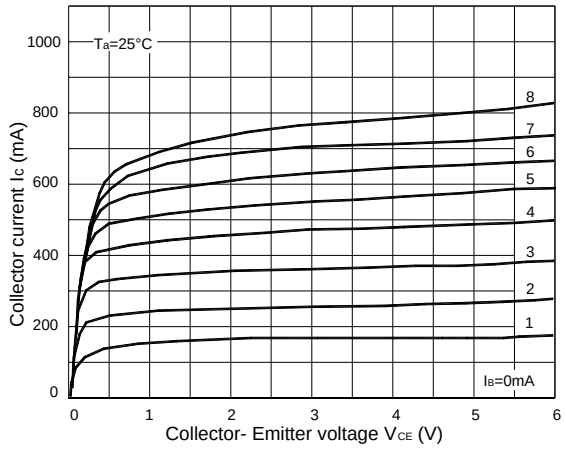

Fig. 4 $V_{CE(sat)}$ - I_C

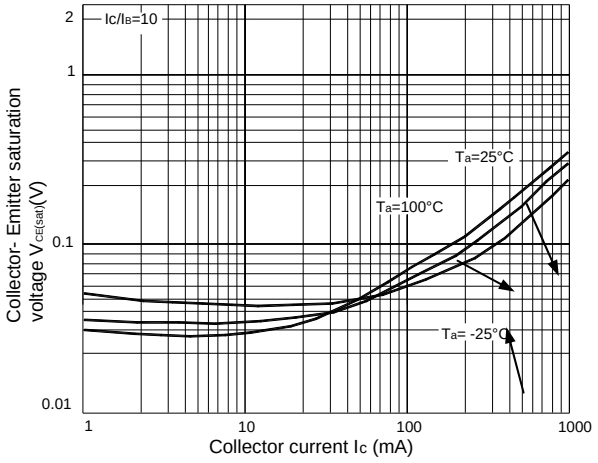

Fig.5 h_{FE} - I_C